

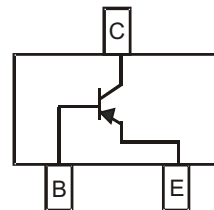
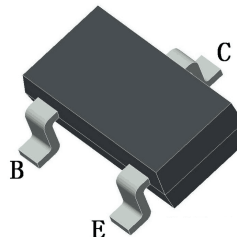
Features

- High voltage transistor

Marking:

- 2D

SOT-23



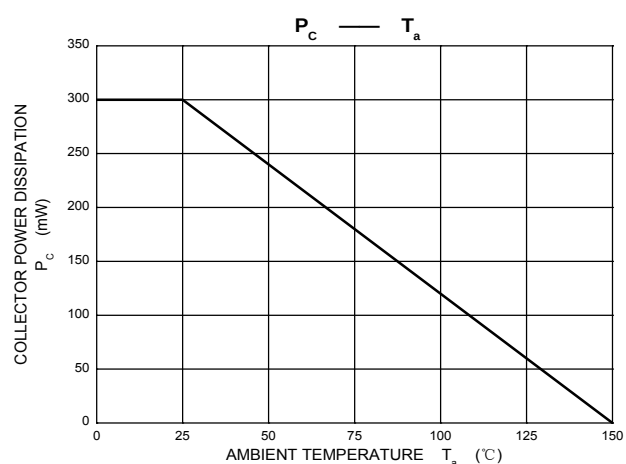
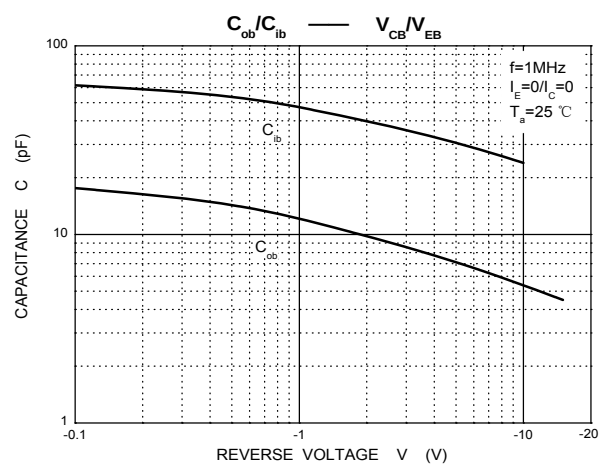
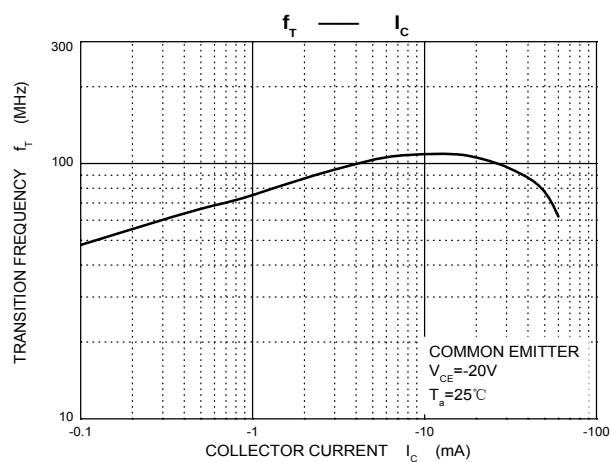
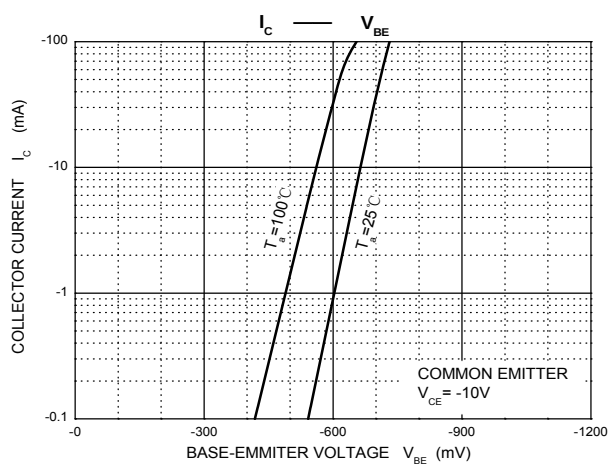
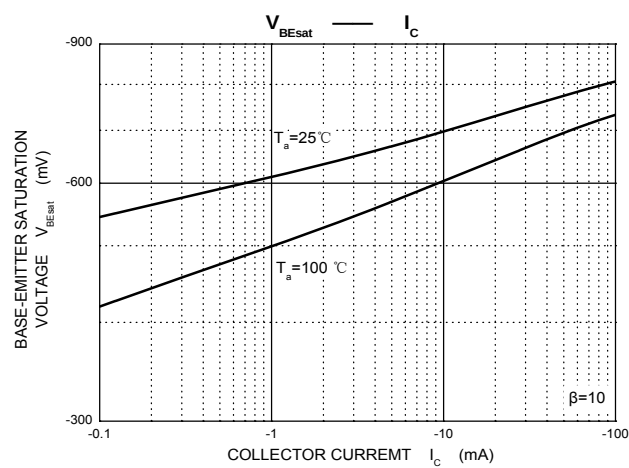
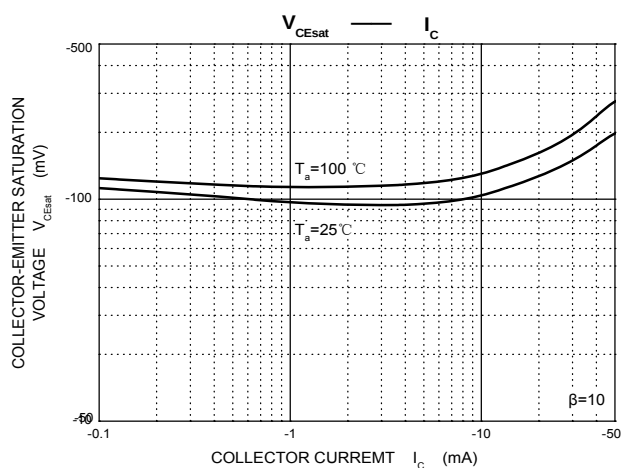
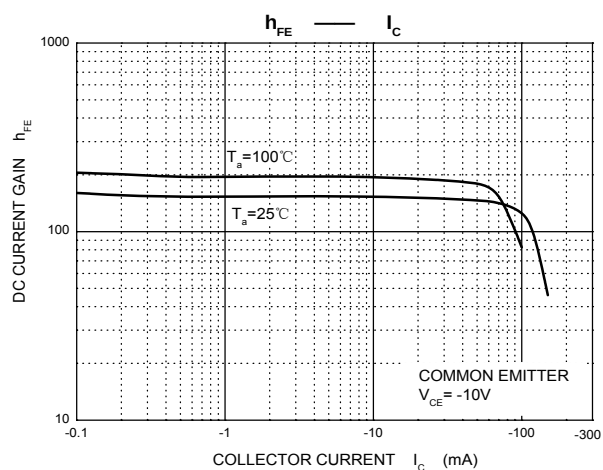
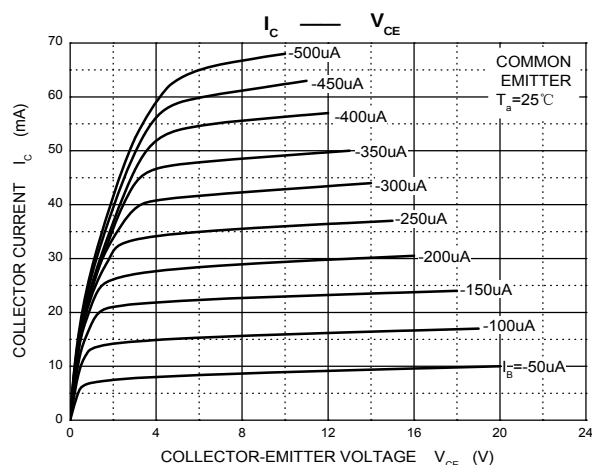
Limiting Values (Absolute Maximum Rating)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-300	V
V_{CEO}	Collector-Emitter Voltage	-300	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-200	mA
I_{CM}	Collector Current - Pulsed	-500	mA
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	417	°C/W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

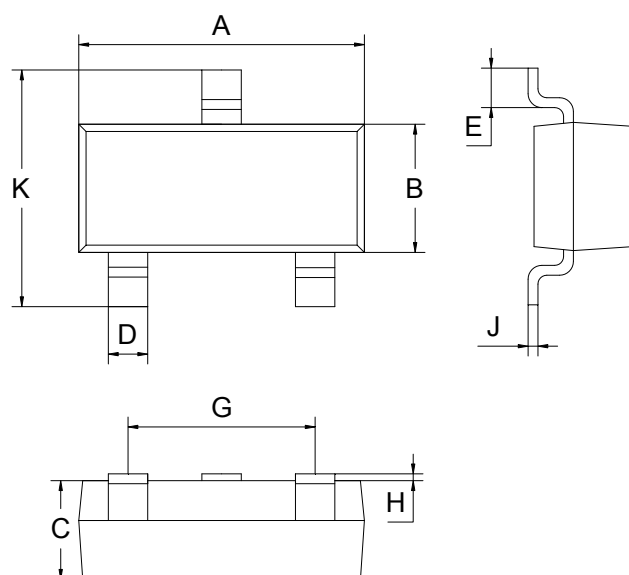
Electrical Characteristics (Ta=25°C Unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -200V, I_E = 0$		-0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -1mA$	60		
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -10mA$	100	200	
	$h_{FE(3)}$	$V_{CE} = -10V, I_C = -30mA$	60		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20mA, I_B = -2mA$		-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20mA, I_B = -2mA$		-0.9	V
Transition frequency	f_T	$V_{CE} = -20V, I_C = -10mA$ $f = 30MHz$	50		MHz

Typical Characteristics

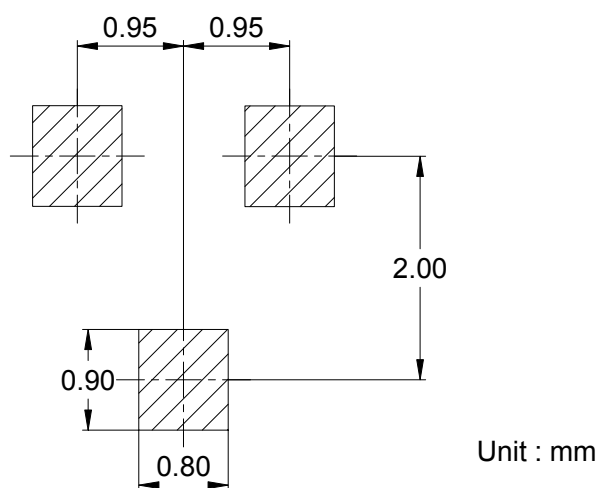


SOT-23 Package Outline Dimensions



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60
All Dimensions in mm		

SOT-23 Suggested Pad Layout



Package Information

TYPE	REEL	Reel Size	Box	Carton
MMBTA92	3000 pcs	7 Inch	45,000 pcs	180,000 pcs